

CLAIMS

1. A ceramic substrate for a semiconductor-producing/examining device having a conductor formed on a surface of said ceramic substrate or inside said ceramic substrate, wherein said substrate is containing oxygen and has a disc form,
the diameter thereof exceeding 250 mm and a thickness thereof being 25 mm or less.
2. The ceramic substrate for a semiconductor-producing/examining device according to claim 1, wherein said ceramic is a nitride ceramic or an oxide ceramic.
3. The ceramic substrate for a semiconductor-producing/examining device according to claim 1, wherein said ceramic is a carbide ceramic.
4. The ceramic substrate for a semiconductor-producing/examining device according to any of claims 1 to 3, wherein said ceramic substrate is used in a temperature range of 100 to 700 °C.
5. The ceramic substrate for a semiconductor-producing/examining device according to any of claims 1 to 4, wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.
6. The ceramic substrate for a semiconductor-producing/examining device according to any of claims 1 to 5, wherein said conductor is formed in a region up to the

position of 60% in a thickness-direction from the face opposite to a wafer treating face of said ceramic substrate.

7. A ceramic substrate for a

5 semiconductor-producing/examining device having a conductor formed on a surface of said ceramic substrate, wherein said substrate has a disc form,

the diameter thereof exceeding 250 mm and a thickness thereof being 25 mm or less.

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8. The ceramic substrate for a

semiconductor-producing/examining device according to claim 7, wherein said ceramic is a nitride ceramic containing oxygen or an oxide ceramic.

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9. The ceramic substrate for a

semiconductor-producing/examining device according to claim 7, wherein said ceramic is a carbide ceramic containing oxygen.

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10. The ceramic substrate for a

semiconductor-producing/examining device according to any of claims 7 to 9,

25 wherein a conductor is formed on the face opposite to a wafer treating face.

11. The ceramic substrate for a

semiconductor-producing/examining device according to any of claims 7 to 10,

30 wherein said ceramic substrate is used in a temperature range of 100 to 700 °C.

12. The ceramic substrate for a

35 semiconductor-producing/examining device according to any of claims 7 to 11,

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wherein said ceramic substrate has a plurality of through holes in which lifter pins for a semiconductor wafer are inserted.

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